

# **Notice of References Cited**

Application/Control No.

09/437,135

Applicant(s)/Patent Under  
Reexamination  
YAMAZAKI ET AL.

Examiner

Erik Kielin

Art Unit

2813

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## **U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-5,000,113	03-1991	Wang et al.	118/723E
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

## **FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
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	Q					
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	S					
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## **NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Jiang et al. "Study of n-channel enhancement mode InP MISFETs" Chinese Journal of Semiconductors 9(5), September 1988, pp. 451-458.
	V	Sun et al. "High Quality MOSFET's with N2O Annealed Thin TEOS Gate Oxide" IEEE 1993 International Symposium on VLSI Technology, May 1993, pp. 109-111.
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.